

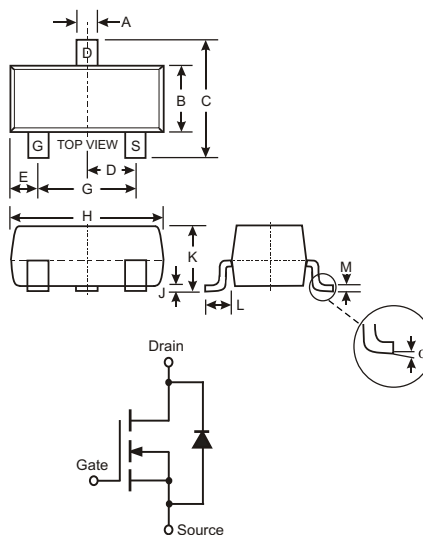
## N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### Features

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating
- Lead Free/RoHS Compliant (Note 2)**

### Mechanical Data

- Case: SOT-23  
Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0  
Moisture Sensitivity: Level 1 per J-STD-020C  
Terminals: Solderable per MIL-STD-202, Method 208  
Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).  
Terminal Connections: See Diagram  
Marking: K23 (See Page 3)  
Ordering & Date Code Information: See Page 3  
Weight: 0.008 grams (approximate)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
	0	8
All Dimensions in mm		

### Maximum Ratings @ T<sub>A</sub> = 25 °C unless otherwise specified

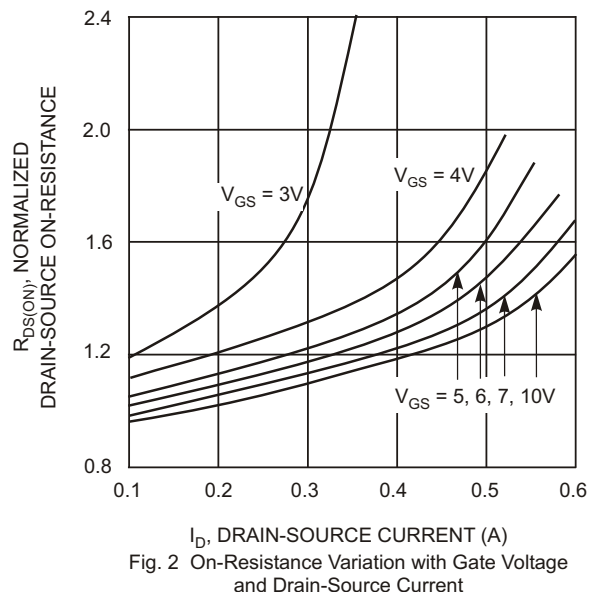
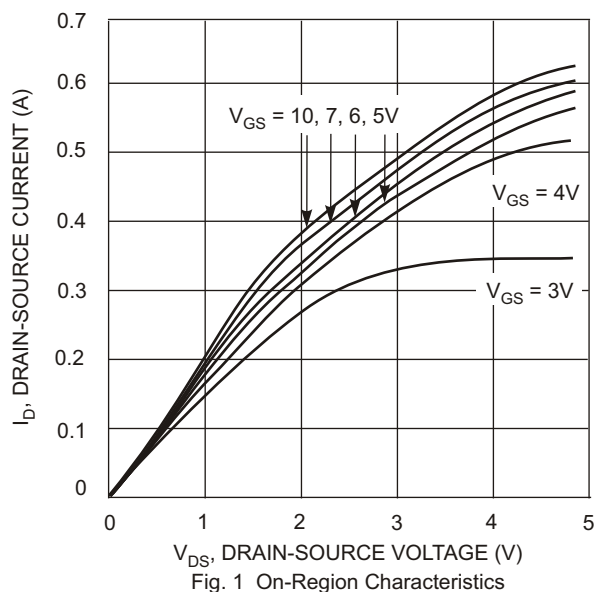
Characteristic	Symbol	BSS123	Units
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Drain-Gate Voltage R <sub>GS</sub> = 20K	V <sub>DGR</sub>	100	V
Gate-Source Voltage Continuous	V <sub>GSS</sub>	20	V
Drain Current (Note 1) Continuous Pulsed	I <sub>D</sub> I <sub>DM</sub>	170 680	mA
Total Power Dissipation (Note 1)	P <sub>d</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>JA</sub>	417	C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	C

- Note: 1. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.  
2. No purposefully added lead.

## Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100			V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250 A
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1.0 10	μA nA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Body Leakage, Forward	I <sub>GSSF</sub>			50	nA	V <sub>GS</sub> = 20V, V <sub>DS</sub> = 0V
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.8	1.4	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>			6.0 10		V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.17A V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.17A
Forward Transconductance	g <sub>FS</sub>	80	370		mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.17A, f = 1.0KHz
Drain-Source Diode Forward Voltage	V <sub>SD</sub>		0.84	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.34A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C <sub>iss</sub>		29	60	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>		10	15	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		2	6	pF	
SWITCHING CHARACTERISTICS						
Turn-On Rise Time	t <sub>r</sub>			8	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.28A, R <sub>GEN</sub> = 50 , V <sub>GS</sub> = 10V
Turn-Off Fall Time	t <sub>f</sub>			16	ns	
Turn-On Delay Time	t <sub>D(ON)</sub>			8	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>			13	ns	

Note: 3. Short duration test pulse used to minimize self-heating effect.



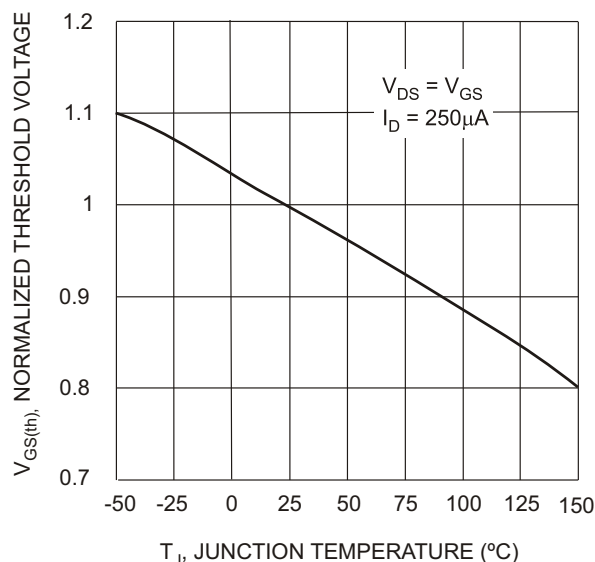


Fig. 3 Gate Threshold Variation with Temperature

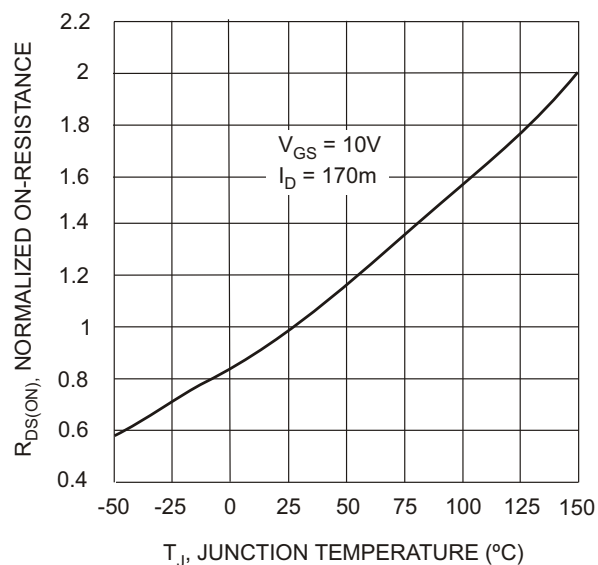


Fig. 4 On-Resistance Variation with Temperature

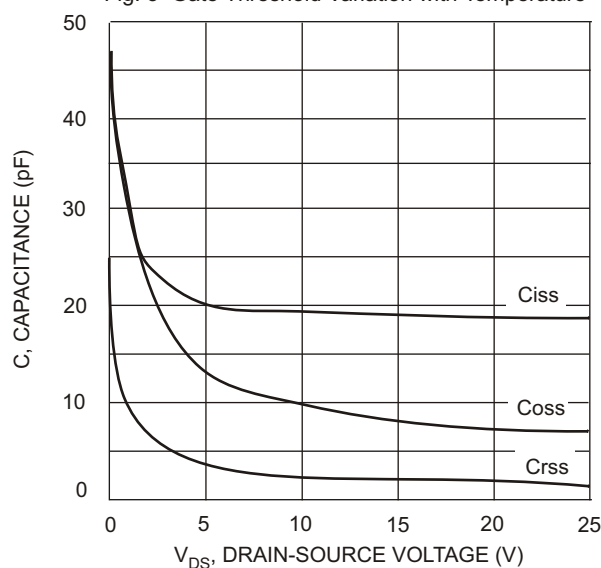


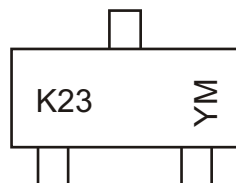
Fig. 5 Typical Capacitance

## Ordering Information (Note 4)

Device	Packaging	Shipping
BSS123-7-F	SOT-23	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

## Marking Information



K23 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: N = 2002  
 M = Month ex: 9 = September

### Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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